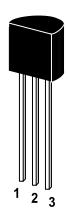
NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}C$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	I _C	800	mA
Base Current	I _B	160	mA
Power Dissipation	P _{tot}	600	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







ST 2SC2120

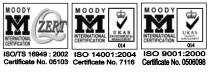
Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at $V_{CE}=1V$, $I_{C}=100mA$					
Current Gain Group O	h_{FE}	100	-	200	-
Υ	h_{FE}	160	-	320	-
at V _{CE} =1V, I _C =700mA	h_{FE}	35	-	-	-
Collector Cutoff Current					
at V _{CB} =35V	I _{CBO}	-	-	0.1	μΑ
Emitter Cutoff Current					
at V _{EB} =5V	I_{EBO}	-	-	0.1	μΑ
Collector Emitter Saturation Voltage					
at I _C =500mA, I _B =20mA	$V_{CE(sat)}$	-	-	0.5	V
Transition Frequency					
at V_{CE} =5V, I_{C} =10mA	f_T	-	120	-	MHz
Base Emitter Voltage					
at I _C =10mA, V _{CE} =1V	V_{BE}	0.5	-	0.8	V
Collector Output Capacitance					
at V _{CB} =10V, f=1MHz	C_OB	-	13	-	pF
Collector Emitter Breakdown Voltage					
at I _C =10mA	V_{CEO}	30	-	-	V

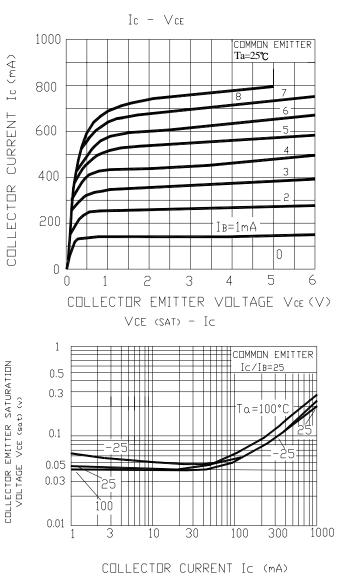


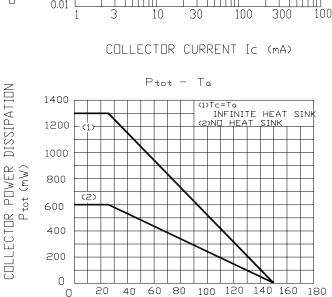




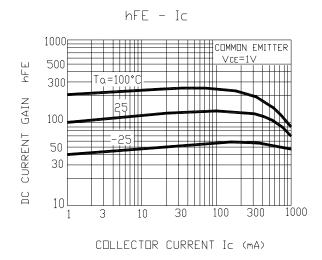


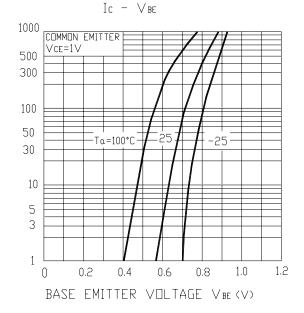
SEMTECH ELECTRONICS LTD.





AMBIENT TEMPERATURE Ta ()





CURRENT Ic (mA)

COLLECTOR



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)





